

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

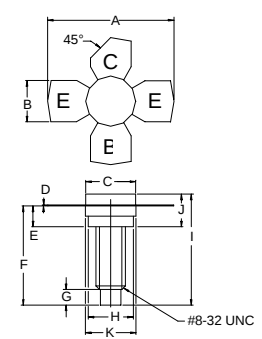
The **ASI ULBM10** is Designed for Class C, FM Land Mobile Applications up to 470 MHz.

FEATURES:

- Common Emitter
- $P_G = 7.0$ dB at 10 W/470 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	2.5 A
V_{CBO}	36 V
V_{CEO}	16 V
V_{CES}	36 V
V_{EBO}	4.0 V
P_{DISS}	58 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	7.0°C/W

PACKAGE STYLE .280 4L STUD		
		
DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24
ORDER CODE: ASI10682		

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 20$ mA	16			V
BV_{CES}	$I_C = 25$ mA	36			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CEO}	$V_{CB} = 15$ V			2.0	mA
I_{CES}	$V_{CE} = 10$ V			3.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		---	---
C_{ob}	$V_{CB} = 12.5$ V $f = 1.0$ MHz			25	pF
P_G η_C	$V_{CC} = 12.5$ V $P_{OUT} = 10$ W $f = 470$ MHz	7.0	60		dB %